Notice of Allowability	Application No.	Applicant(s)	Applicant(s)	
	10/645,529	KOKUBUN, KOICHI		
	Examiner	Art Unit		
	Hoai V Pham	2814		
Th MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED or other appropriate comm GHTS. This application is	ith the correspondence addre	ed course THIS	
1. X This communication is responsive to 22 August 2003.				
2. The allowed claim(s) is/are 7-18.				
3. The drawings filed on 22 August 2003 are accepted by the	Examiner.			
 4. Acknowledgment is made of a claim for foreign priority un a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 	been received.	-		
2. Continued copies of the priority documents have				
 Copies of the certified copies of the priority doc International Bureau (PCT Rule 17.2(a)). 	uments have been receive	ed in this national stage applicat	ion from the	
* Certified copies not received:			•	
Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONMI THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be submit	ENT of this application.			
INFORMAL PATENT APPLICATION (PTO-152) which give	s reason(s) why the oath o	or declaration is deficient.	JIICE OF	
6. CORRECTED DRAWINGS (as "replacement sheets") must			*.	
(a) ☐ including changes required by the Notice of Draftsperso	on's Patent Drawing Revie	w (PTO-948) attached		
1) hereto or 2) to Paper No./Mail Date				
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	Amendment / Comment o	r in the Office action of		
Identifying indicia such as the application number (see 37 CFR 1.8 each sheet. Replacement sheet(s) should be labeled as such in the			back) of	
 DEPOSIT OF and/or INFORMATION about the depose attached Examiner's comment regarding REQUIREMENT F 	it of BIOLOGICAL MAT OR THE DEPOSIT OF BI	ERIAL must be submitted. N OLOGICAL MATERIAL.	ote the	
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Attachment(s)		• 1		
Notice of References Cited (PTO-892)	5. Notice of Ir	oformal Patent Application (PTC)-152)	
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. 🔲 Interview S	6. Interview Summary (PTO-413), Paper No./Mail Date		
 Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No./Mail Date <u>22 August 2003</u> 	3), 7. ⊠ Examiner's	Amendment/Comment		
B. ☐ Examiner's Comment Regarding Requirement for Deposit		Statement of Reasons for Allov	vance	
of Biological Material	9. 🗍 Other	· ·		
		Waylam Hoai Pham		
		May 21 2004		

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DETAILED ACTION

Examiner's amendment

- 1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.
- 2. The application has been amended as follows:

In the specification:

Change the title to: --METHOD OF MANUFACTURING THE SEMICONDUCTOR

DEVICE HAVING A CAPACITOR FORMED IN SOI SUBSTRATE--.

Page 1, after the "CROSS-REFERENCE TO RELATED APLICATION" insert -- This is a divisional of Application No. 10/178,749 filed June 25, 2002, now U.S. Pat. No. 6,635,915.--.

Allowable Subject Matter

- 3. Claims 7-18 are allowed.
- 4. The following is an examiner's statement of reasons for allowance: the prior of record fails to disclose the combination of the process steps of forming a semiconductor device recited in the base claim 7, including the combination of the process steps comprising: etching back the first insulating film to such a depth as to reach an upper surface of the buried insulating film, using the second insulating film as a mask, and recessing the buried insulating film exposed to the sidewall portion of the trench;

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forming a semiconductor layer by epitaxial growth in a gap created by the recessed buried insulating film. And the prior of record fails to disclose the combination of the process steps of forming a semiconductor device recited in the base claim 13, including the combination of the process steps comprising: etching back the first insulating film to such a depth as to reach an upper surface of the buried insulating film, using the second insulating film as a mask, and recessing the buried insulating film exposed to the sidewall portion of the trench; depositing a polysilicon layer on a major surface of the SOI substrate and in the trench; etching back the polysilicon layer by performing anisotropy etching to cause the polysilicon layer to remain in a gap created by the recessed buried insulating film in the trench.

- 5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hoai V Pham whose telephone number is 571-272-1715. The examiner can normally be reached on 9:30A.M. 8:00P.M..
- 6. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael M. Fahmy can be reached on 571-272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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7. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Hoai Pham

May 21, 2004